

PRODUCT NEWS

Product Discontinuation Notice

Photomicrosensors

October 30, 2010

No. A1PH-095252(E)

Discontinuation Notice of Photomicrosensors.

EE-SB5V series

Product Discontinuation

Recommended Replacement



EE-SB5V Series



Please contact the appropriate division
EE-SY672
(except the EE-SB5M-E)

Discontinuation date : The end of May, 2010

Caution on recommended replacement

Our Amplified photomicrosensors, model EE-SB5V series will be discontinued at the end of May, 2010. We recommend Amplified photomicrosensors, type EE-SY672 for replacement of them (except the EE-SB5V-E). And we recommend to change your products design or to order it collectively including a necessary amount in the future by May, 2010.

Difference from discontinued product

Model	Body Color	Dimensions	Wire connection	Mounting Dimentions	Characteristics	Operation ratings	Operation methods
EE-SY672	**	*	--	*	*	*	**

** : Fully compatible

* : The change is a little / Almost compatible

-- : Not compatible

- : No corresponding specification

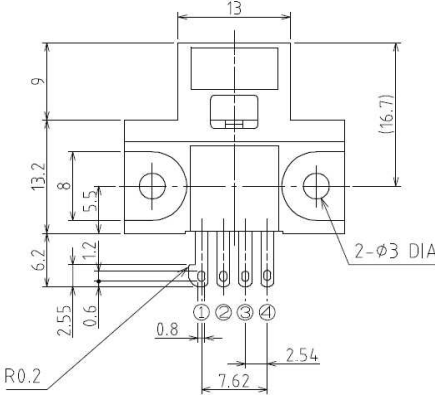
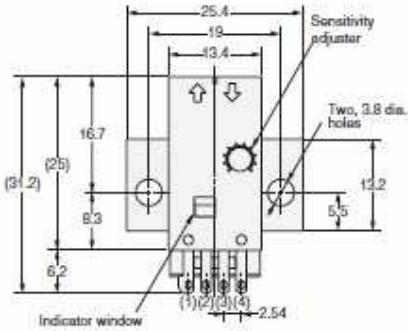
Product Discontinuation and recommended replacement

Product discontinuation		Recommended replacement	
Model	Product code	Model	Product code
EE-SB5V	EESB1010G	EE-SY672	EESY1124M
EE-SB5V-F	EESB5052D	No recommended replacement	
EE-SB5V-P1	EESB5054M	EE-SY672	EESY1124M
EE-SB5VC	EESB2010B	EE-SY672	EESY1124M

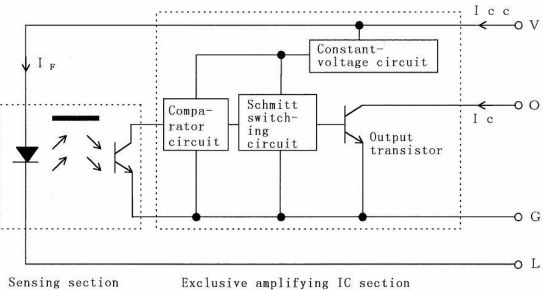
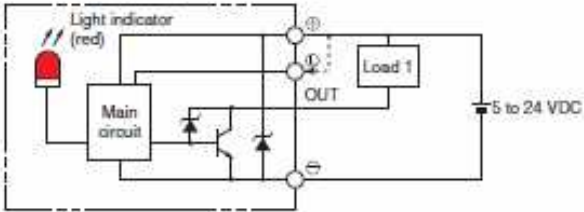
Dimensions

Model to be discontinued EE-SB5V series	Recommended replacement EE-SY672

Terminal dimension

Model to be discontinued EE-SB5V series	Recommended replacement EE-SY672																								
																									
<p>Terminal Arrangement</p> <table><tr><td></td><td>+</td><td>Vcc</td></tr><tr><td></td><td>L</td><td>L</td></tr><tr><td></td><td>OUT</td><td>OUTPUT</td></tr><tr><td></td><td>-</td><td>GND(0V)</td></tr></table>		+	Vcc		L	L		OUT	OUTPUT		-	GND(0V)	<p>Terminal Arrangement</p> <table><tr><td>(1)</td><td>+</td><td>Vcc</td></tr><tr><td>(2)</td><td>L</td><td>L</td></tr><tr><td>(3)</td><td>OUT</td><td>OUTPUT</td></tr><tr><td>(4)</td><td>-</td><td>GND (0 V)</td></tr></table>	(1)	+	Vcc	(2)	L	L	(3)	OUT	OUTPUT	(4)	-	GND (0 V)
	+	Vcc																							
	L	L																							
	OUT	OUTPUT																							
	-	GND(0V)																							
(1)	+	Vcc																							
(2)	L	L																							
(3)	OUT	OUTPUT																							
(4)	-	GND (0 V)																							

Internal connection

Model to be discontinued EE-SB5V series	Recommended replacement EE-SY672
 <p>Sensing section Exclusive amplifying IC section</p>	

Characteristics

Item		Model to be discontinued		Recommended replacement EE-SY672	
		EE-SB5V	EE-SB5VC		
Sensing distance		5mm (Reflection factor 90%)		1 to 5mm (Reflection factor 90%)	
Differential distance		0.1mm		0.5mm	
Light source		GaAs infrared LED		GaAs infrared LED	
Supply voltage		5-10% to 15+10% VDC Ripple (p-p): 10% MAX.		5-10% to 24+10% VDC Ripple (p-p): 10% MAX.	
Current consumption		48mA MAX.		40mA MAX.	
Control output		Load power supply voltage: 5 to 24VDC 80mA load current with a residual voltage 0.8V MAX. 40mA load current with a residual voltage 0.4V MAX.		Load power supply voltage: 5 to 24VDC 100mA load current with a residual voltage 0.8V MAX. 40mA load current with a residual voltage 0.4V MAX.	
Stage of output transistor	Stage of output transistor when object is not sensed	OFF	ON	OFF (Terminal [L] is short-circuited)	ON (Terminal [L] is opened)
	Stage of output transistor when object is sensed	ON	OFF	ON (Terminal [L] is short-circuited)	OFF (Terminal [L] is opened)
Response frequency		50Hz		50Hz	
Ambient temperature range		Operating : -25 ~ +55 Storage : -30 ~ +80		Operating : -25 ~ +55 Storage : -30 ~ +80	
Ambient humidity range		Operating : 45 ~ 85%RH Storage : 35 ~ 95%RH		Operating : 5 ~ 85%RH Storage : 5 ~ 95%RH	
Vibration resistance		Destruction: 20 to 2000 Hz (Peak acceleration: 200m/s ²) 1.5mm double amplitude for 4cycle (4min periods) each in X, Y and Z directions		Destruction: 20 to 2000 Hz (Peak acceleration: 100m/s ²) 1.5mm double amplitude for 2h (4min periods) each in X, Y and Z directions	
Shock resistance		Destruction: 15000m/S ² for 3 times each in X, Y and Z directions		Destruction: 500m/S ² for 3 times each in X, Y and Z directions	

Item		Model to be discontinued EE-SB5V-P1	Recommended replacement EE-SY672	
Sensing distance		5mm (Reflection factor 90%)	1 to 5mm (Reflection factor 90%)	
Differential distance		0.1mm	0.5mm	
Light source		GaAs infrared LED	GaAs infrared LED	
Supply voltage		24 ± 10% VDC	5-10% to 24+10% VDC Ripple (p-p): 10% MAX.	
Current consumption		-	40mA MAX.	
Control output		Load power supply voltage: 5 to 24VDC 10mA load current with a residual voltage 0.3V MAX.	Load power supply voltage: 5 to 24VDC 100mA load current with a residual voltage 0.8V MAX. 40mA load current with a residual voltage 0.4V MAX.	
Stage of output transistor	Stage of output transistor when object is not sensed	OFF	OFF (Terminal [L] is short-circuited)	ON (Terminal [L] is opened)
	Stage of output transistor when object is sensed	ON	ON (Terminal [L] is short-circuited)	OFF (Terminal [L] is opened)
Response frequency		50Hz	50Hz	
Ambient temperature range		Operating : -25 ~ +55 Storage : -30 ~ +80	Operating : -25 ~ +55 Storage : -30 ~ +80	
Ambient humidity range		Operating : 45 ~ 85%RH Storage : 35 ~ 95%RH	Operating : 5 ~ 85%RH Storage : 5 ~ 95%RH	
Vibration resistance		Destruction: 20 to 2000 Hz (Peak acceleration: 200m/s ²) 1.5mm double amplitude for 4cycle (4min periods) each in X, Y and Z directions	Destruction: 20 to 2000 Hz (Peak acceleration: 100m/s ²) 1.5mm double amplitude for 2h (4min periods) each in X, Y and Z directions	
Shock resistance		Destruction: 15000m/S ² for 3 times each in X, Y and Z directions	Destruction: 500m/S ² for 3 times each in X, Y and Z directions	

Item		Model to be discontinued EE-SB5V-E	Recommended replacement No type
Sensing distance		19mm (Reflection factor 90%)	
Differential distance		0.1mm	
Light source		GaAs infrared LED	
Supply voltage		5-10% to 15+10% VDC Ripple (p-p): 10% MAX.	
Current consumption		48mA MAX.	
Control output		Load power supply voltage: 5 to 24VDC 80mA load current with a residual voltage 0.8V MAX. 40mA load current with a residual voltage 0.4V MAX.	
Stage of output transistor	Stage of output transistor when object is not sensed	OFF	
	Stage of output transistor when object is sensed	ON	
Response frequency		50Hz	
Ambient temperature range		Operating : -25 ~ +55 Storage : -30 ~ +80	
Ambient humidity range		Operating : 45 ~ 85%RH Storage : 85 ~ 95%RH	
Vibration resistance		Destruction: 20 to 2000 Hz (Peak acceleration: 200m/s ²) 1.5mm double amplitude for 4cycle (4min periods) each in X, Y and Z directions	
Shock resistance		Destruction: 15000m/S ² for 3 times each in X, Y and Z directions	